L Number	Hits	Search Text	DB	Time stamp
1	13657	((438/149) or (438/174) or (438/176) or (438/180) or (438/181) or (438/184) or (438/185) or (438/197) or (438/199) or (438/201) or (438/207) or (438/211) or (438/213) or (438/217) or (438/218) or (438/221) or (438/222) or (438/229) or (438/230) or (438/231) or (438/233) or (438/260) or (438/265) or (438/276) or (438/289) or (438/294) or (438/296) or (438/299) or (438/300) or (438/301) or (438/303) or (438/311) or (438/318) or (438/320) or (438/364) or (438/406) or (438/413) or (438/416) or (438/429) or (438/430) or (438/459) or (438/488) or (438/491) or (438/532) or (438/597) or (438/607) or (438/704)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/31 20:26
2	31127	soi or (silicon near2 insulator)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/31 20:28
3	109204	cmos or (complementary near (metal near2 oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/31 20:31
4	2814	simox or (separation adj ion adj implantation adj oxygen)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/31 20:32
5	1333	(front and back) near5 gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/31 20:33
6	154699	gate near5 (dielectric or insulat$3 or oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/31 20:34
7	85681	trench$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/31 20:34
8	4	sacrifical near3 spacer$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/31 21:21
9	10	sacrifical same spacer$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/31 20:35
10	7641	(soi or (silicon near2 insulator)) and (cmos or (complementary near (metal near2 oxide)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/31 20:36
11	1178	((soi or (silicon near2 insulator)) and (cmos or (complementary near (metal near2 oxide)))) and (simox or (separation adj ion adj implantation adj oxygen))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/31 20:43
12	32	(((soi or (silicon near2 insulator)) and (cmos or (complementary near (metal near2 oxide)))) and (simox or (separation adj ion adj implantation adj oxygen))) and ((front and back) near5 gate)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/31 20:43

13	32	((((soi or (silicon near2 insulator)) and (cmos or (complementary near (metal near2 oxide)))) and (simox or (separation adj ion adj implantation adj oxygen))) and ((front and back) near5 gate))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/31 20:44
16	0	((((((soi or (silicon near2 insulator)) and (cmos or (complementary near (metal near2 oxide)))) and (simox or (separation adj ion adj implantation adj oxygen))) and ((front and back) near5 gate)) and (gate near5 (dielectric or insulat$3 or oxide))) and trench$2) and (sacrifical same spacer$1)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/31 20:45
15	16	(((((soi or (silicon near2 insulator)) and (cmos or (complementary near (metal near2 oxide)))) and (simox or (separation adj ion adj implantation adj oxygen))) and ((front and back) near5 gate)) and (gate near5 (dielectric or insulat$3 or oxide))) and trench$2	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/31 20:53
17	1	((((((soi or (silicon near2 insulator)) and (cmos or (complementary near (metal near2 oxide)))) and (simox or (separation adj ion adj implantation adj oxygen))) and ((front and back) near5 gate)) and (gate near5 (dielectric or insulat$3 or oxide))) and trench$2) and (((438/149) or (438/174) or (438/176) or (438/180) or (438/181) or (438/184) or (438/185) or (438/197) or (438/199) or (438/201) or (438/207) or (438/211) or (438/213) or (438/217) or (438/218) or (438/221) or (438/222) or (438/229) or (438/230) or (438/231) or (438/233) or (438/260) or (438/265) or (438/276) or (438/289) or (438/294) or (438/296) or (438/299) or (438/300) or (438/301) or (438/303) or (438/311) or (438/318) or (438/320) or (438/364) or (438/406) or (438/413) or (438/416) or (438/429) or (438/430) or (438/459) or (438/488) or (438/491) or (438/532) or (438/597) or (438/607) or (438/704)).CCLS.)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/31 20:47
18	9	("6074209" | "6275094" | "6359312" | "6383904" | "6391695" | "6392277" | "6423599" | "6432754" | "6441436").PN.	USPAT	2004/07/31 21:11
37	16	("3853633" | "4222062" | "4393578" | "4839707" | "4951123" | "5166765" | "5273921" | "5285352" | "5376578" | "5482871" | "5726459" | "5780912" | "6008126" | "6057555" | "6074920" | "6166412").PN.	USPAT	2004/07/31 21:14
38	9	("6074209" | "6275094" | "6359312" | "6383904" | "6391695" | "6392277" | "6423599" | "6432754" | "6441436").PN.	USPAT	2004/07/31 21:17
45	7	("5164805" | "5885887" | "6204138" | "6284594" | "6359298" | "6365450" | "6376312").PN.	USPAT	2004/07/31 21:19
46	350479	spacer$1	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/31 21:21
47	9	("4601779" | "5273921" | "5296727" | "5461250" | "5497019" | "5604368" | "5681775" | "5929479" | "6248637").PN.	USPAT	2004/07/31 21:23
14	32	(((((soi or (silicon near2 insulator)) and (cmos or (complementary near (metal near2 oxide)))) and (simox or (separation adj ion adj implantation adj oxygen))) and ((front and back) near5 gate)) and (gate near5 (dielectric or insulat$3 or oxide))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/31 21:28
62	4	("5291047" | "5446299" | "5488243" | "5751037").PN.	USPAT	2004/07/31 21:31

| 63 | 19 | 5929479.URPN. | USPAT | 2004/07/31 21:32 |